

Sub  
C1  
and

~~a grade composition layer provided between the active layer and the third semiconductor layer to have a varying composition,~~

wherein the composition of the grade composition layer is equal to a composition of the third semiconductor layer at an interface with the third semiconductor layer, and to a composition of the active layer at an interface with the active layer.

Cont'd  
B4  
Please add the following new claims 12-22:

--12. (New) The semiconductor light-emitting device of claim 1, wherein the composition at the grade composition layer varies continuously.

13. (New) The semiconductor light-emitting device of claim 1, wherein the composition of the grade composition layer varies stepwise.

B5  
~~14. (New) The semiconductor light-emitting device of claim 1 further comprises a base electrode interposed between the grade composition layer and the active layer, and electrically connected to the third semiconductor layer.~~

Sub  
C2  
~~15. (New) The semiconductor light-emitting device of claim 14, wherein regions of the active layer and the graded composition layer lying between the base electrode and the second semiconductor layer are removed.~~

16. (New) The semiconductor light-emitting device of claim 1, wherein during a light-emitting period, a forward bias voltage is applied between the third semiconductor layer and the second semiconductor layer, and the potential between the third semiconductor layer and the first semiconductor layer is adjusted to 0.

17. (New) The semiconductor light-emitting device of claim 1, wherein during an extinction period, a reverse bias voltage is applied between the third semiconductor layer and the first semiconductor layer.

18. (New) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is n-type.

19. (New) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is device of p-type.

SJG 3  
Cont'd  
BS  
20. (New) ~~The semiconductor light-emitting device of claim 14, wherein the third semiconductor layer is p-type.~~

21. (New) The semiconductor light-emitting device of claim 20, wherein a high-resistance region is provided in a region that opposed to the base electrode in the second semiconductor layer but not opposed layer to the first semiconductor layer.

22. (New) The semiconductor light-emitting device of claim 21, wherein the high-resistance region is formed by ion implantation.--

#### REMARKS

At the outset the Examiner is thanked for the review and consideration of the present application, and for indicating that claims 2-11 have been withdrawn from consideration as being drawn to a non-elected species.

The Examiner's Action dated September 12, 2002 has been received and its contents reviewed. By this amendment, claim 1 has been amended, and claims 12-22 have been newly added. . Accordingly, claims 1, and 12-22 are pending in the instant application for consideration, of which claim 1 is independent.

Turning now to the detailed Office Action, the drawings are objected to as Figs 17-20 are not labeled as "Prior Art". In response, Applicants respectfully submit that Figs. 17-20 are properly labeled as "Prior Art", according to Applicants' record. Hence, Applicants would like to confirm if there are actual errors in the drawings submitted with the original application. If so, Applicants would correct any errors in the drawings as necessary.

The specification is objected to as failing to delineate what is meant by "nearly" in the phrase "nearly equal to a composition of the active layer" which is found in page 6, line 20, page 19, line 13, and page 22, line 17 of the specification. In response, Applicants have amended the